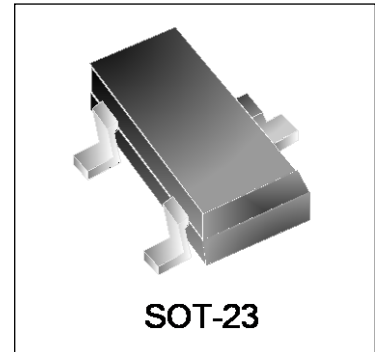


Features

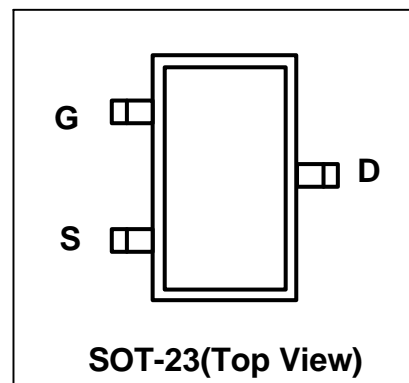
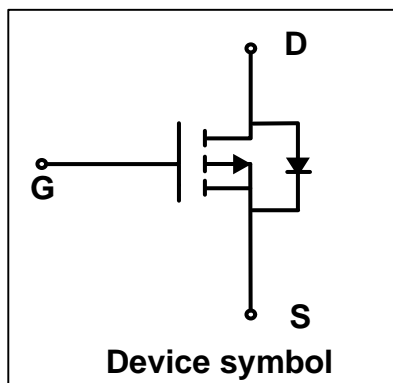
- Way-on Small Single MOSFETs
- $V_{DS} = -20V$, $I_D = -3A$
 $R_{DS(ON)} < 70m\Omega @ V_{GS} = -4.5V$
 $R_{DS(ON)} < 90m\Omega @ V_{GS} = -2.5V$
- Trench LV MOSFET Technology

Mechanical Characteristics

- SOT-23 Package
- Marking : Making Code
- RoHS Compliant



Schematic & PIN Configuration



Absolute Maximum Rating ($T_A=25^\circ C$ unless otherwise noted)

Rating	Symbol	Value	Units
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current	I_D	-3	A
Pulsed Drain Current ¹	I_{DM}	-10	A
Power Dissipation	P_D	1	W
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ C$

Thermal Characteristics

Rating	Symbol	Value	Units
Thermal Resistance from Junction to Ambient ²	$R_{\theta JA}$	125	$^\circ C/W$

Electrical Characteristics (T_J=25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Units
Static Characteristics						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = -250μA	-20	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -20V, V _{GS} = 0V	-	-	-1	μA
Gate-Source Leakage	I _{GSS}	V _{DS} = 0V, V _{GS} = ±12V	-	-	±100	nA
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250μA	-0.4	-	-1	V
Drain-Source on-State Resistance ³	R _{DS(on)}	V _{GS} = -4.5V, I _D = -3.0A	-	50	70	mΩ
		V _{GS} = -2.5V, I _D = -2.0A	-	60	90	
Dynamic Characteristics⁴						
Input Capacitance	C _{iss}	V _{GS} = 0V, V _{DS} = -10V, f=1.0MHz	-	616	-	pF
Output Capacitance	C _{oss}		-	75	-	
Reverse Transfer Capacitance	C _{rss}		-	65	-	
Switching Characteristics⁴						
Total gate charge	Q _g	V _{GS} = -2.5V, V _{DS} = -10V, I _D = -3A	-	3.3	-	nC
Gate-source charge	Q _{gs}		-	0.7	-	
Gate-drain charge	Q _{gd}		-	1.3	-	
Turn-on Time	t _{d(on)}	V _{GS} = -4.5V, V _{DD} = -10V, R _L = 10Ω, R _{GEN} = 1Ω	-	11	-	ns
Rise Time	t _r		-	35	-	
Turn-off Time	t _{d(off)}		-	30	-	
Fall Time	t _f		-	10	-	
Source-Drain Diode Characteristics						
Body Diode Voltage	V _{SD}	I _S = -1A, V _{GS} = 0V	-	-	-1.2	V
Continuous Source Current	I _S		-	-	-3	A

Notes:

1. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C.
2. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.
3. Pulse Test: Pulse width≤300μs, duty cycle≤2%.
4. This value is guaranteed by design hence it is not included in the production test.

Typical Characteristics

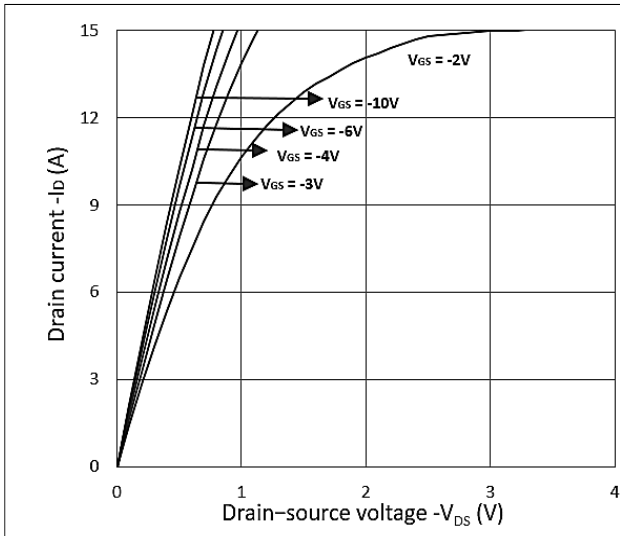


Figure 1. Output Characteristics

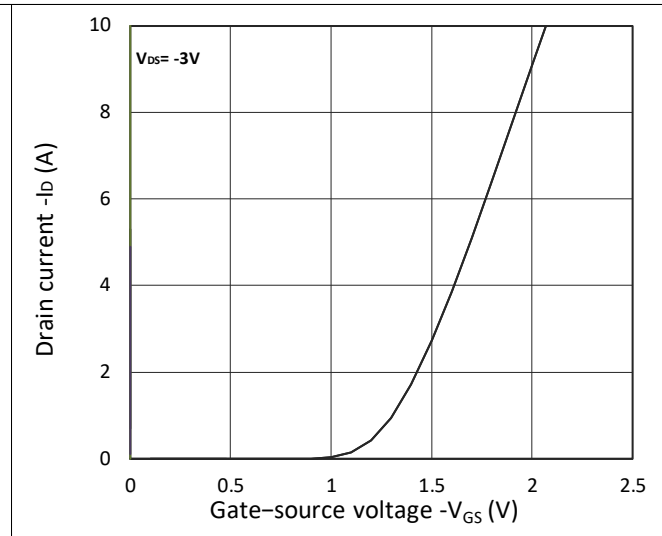


Figure 2. Transfer Characteristics

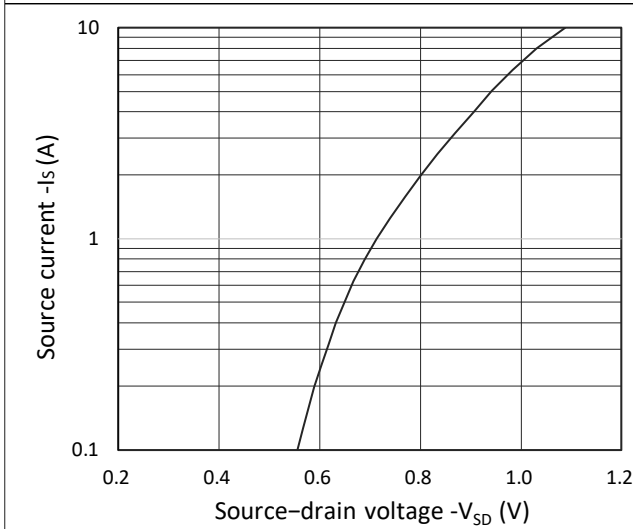


Figure 3. Forward Characteristics of Reverse

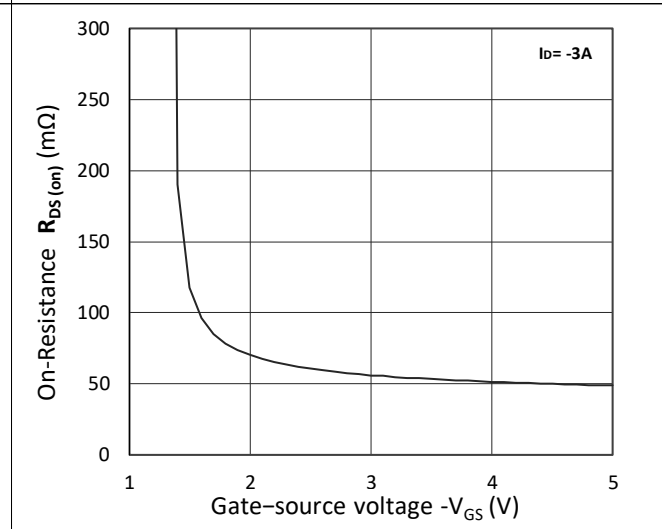


Figure 4. $R_{DS(ON)}$ vs. V_{GS}

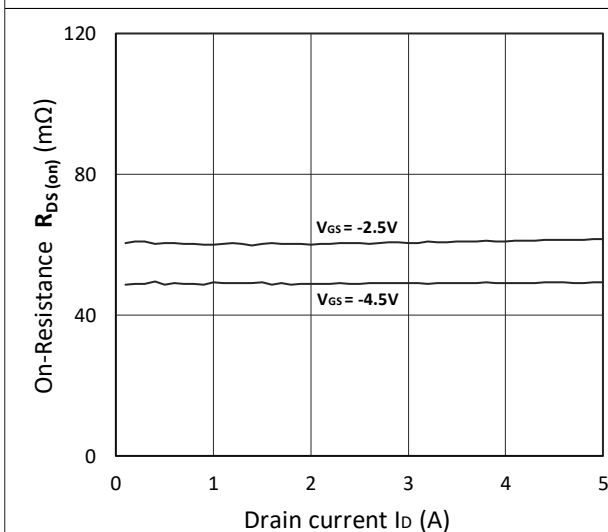


Figure 5. $R_{DS(ON)}$ vs. I_D

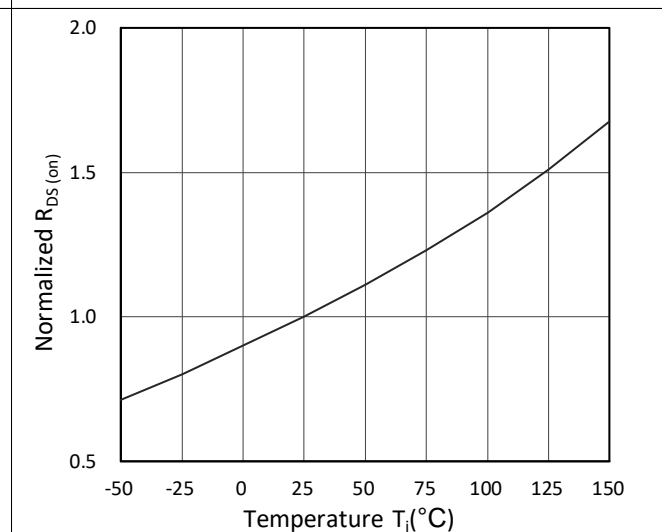


Figure 6. Normalized $R_{DS(ON)}$ vs. Temperature

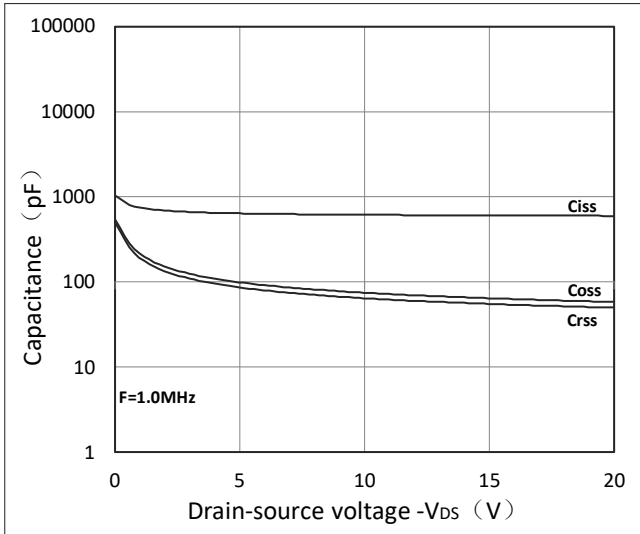


Figure 7. Capacitance Characteristics

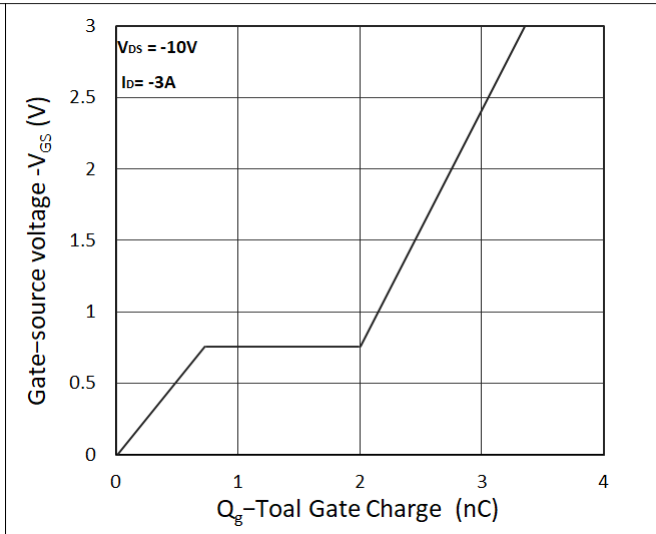


Figure 8. Gate Charge Characteristics

Outline Drawing – SOT-23

PACKAGE OUTLINE

SOT-23

SYMBOL	MILLIMETER		INCHES	
	MIN	MAX	MIN	MAX
A	0.90	1.15	0.035	0.045
A1	0.00	0.10	0.000	0.004
b	0.30	0.50	0.012	0.020
c	0.08	0.15	0.003	0.006
D	2.80	3.00	0.110	0.118
E	2.25	2.55	0.089	0.100
E1	1.20	1.40	0.047	0.055
e	0.95 BSC		0.037BSC	
e1	1.80	2.00	0.071	0.079
L	0.55REF		0.022REF	
θ	0°	8°	0°	8°

DIMENSIONS		
DIM	INCHES	MILLIMETERS
M	0.080	2.02
C	0.032	0.80
Z	0.111	2.82
e	0.037 BSC	0.95 BSC
e1	0.075 BSC	1.90 BSC
b	0.032	0.80

Notes

1. Dimensioning and tolerances per ANSI Y14.5M, 1985.
2. Controlling Dimension: Inches
3. Pin 3 is the cathode (Unidirectional Only).
4. Dimensions are exclusive of mold flash and metal burrs.

Marking Codes

Part Number	WM02P30M
Marking Code	

Package Information

Qty: 3k/Reel

CONTACT INFORMATION

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Specifications are subject to change without notice.
 The device characteristics and parameters in this data sheet can and do vary in different applications and actual device performance may vary over time.
 Users should verify actual device performance in their specific applications.